

# MOSFET - Power, Single N-Channel 35 V, 104 mΩ, 3 A CPH3455

# Description

This Power MOSFET is produced using **onsemi**'s trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

#### **Features**

- Low On-Resistance
- 4V Drive
- Pb-Free, Halogen Free and RoHS Compliance

#### **Typical Applications**

- Load Switch
- Motor Drive

#### MAXIMUM RATINGS (T<sub>.I</sub> = 25°C unless otherwise noted) (Note 1)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	35	V
Gate-to-Source Voltage	$V_{GSS}$	±20	V
Drain Current (DC)	I <sub>D</sub>	3	Α
Drain Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I <sub>DP</sub>	12	Α
Power Dissipation When mounted on ceramic substrate (900 mm² x 0.8 mm)	P <sub>D</sub>	1	V
Junction Temperature	Tj	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

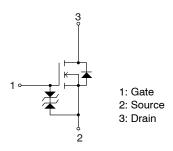
Parameter	Symbol	Value	Unit
Junction-to-Ambient When mounted on ceramic substrate (900 mm <sup>2</sup> x 0.8 mm)	$R_{\theta JA}$	125	°C/W

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
35 V	104 mΩ @ 10 V	3 A
	173 mΩ @ 4.5 V	
	208 mΩ @ 4 V	

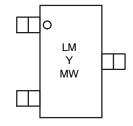


CPH3 CASE 318BA

# ELECTRICAL CONNECTION N-Channel



# **MARKING DIAGRAM**



LM = Specific Device Code

Y = Year M = Month W = Week

#### **ORDERING INFORMATION**

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

This product is designed to "ESD immunity <200 V\*", so please take care when handling.

<sup>\*</sup>Machine Model

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Drain to Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V	35	-	-	V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 35 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ
Gate to Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	-		±10	μΑ
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.2	-	2.6	V
Forward Transconductance	9FS	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.5 A	-	1.7	-	S
Static Drain to Source On-State Resistance	R <sub>DS(on)</sub> 1	I <sub>D</sub> = 1.5 A, V <sub>GS</sub> = 10 V	-	80	104	mΩ
	R <sub>DS(on)</sub> 2	I <sub>D</sub> = 0.75 A, V <sub>GS</sub> = 4.5 V	-	123	173	mΩ
	R <sub>DS(on)</sub> 3	I <sub>D</sub> = 0.75 A, V <sub>GS</sub> = 4 V	-	148	208	mΩ
Input Capacitance	Ci <sub>SS</sub>	V <sub>DS</sub> = 20 V, f = 1 MHz	-	186	-	pF
Output Capacitance	Co <sub>SS</sub>		_	36	-	
Reverse Transfer Capacitance	Cr <sub>SS</sub>		_	22	-	
Turn-On Delay Time	t <sub>d(on)</sub>	See specified Test Circuit	-	4.2	-	ns
Rise Time	t <sub>r</sub>		-	4.7	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	-	
Fall Time	t <sub>f</sub>	1	-	5.7	-	
Total Gate Charge	Qg	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3 A	-	4	-	nC
Gate-to-Source Charge	Q <sub>gs</sub>		-	0.9	-	
Gate to Drain "Miller" Charge	Q <sub>gd</sub>		-	0.7	_	
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 3 A, V <sub>GS</sub> = 0 V	_	0.86	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **SWITCHING TIME TEST CIRCUIT**

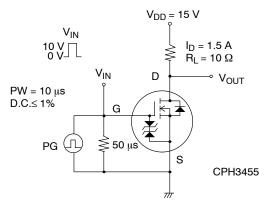
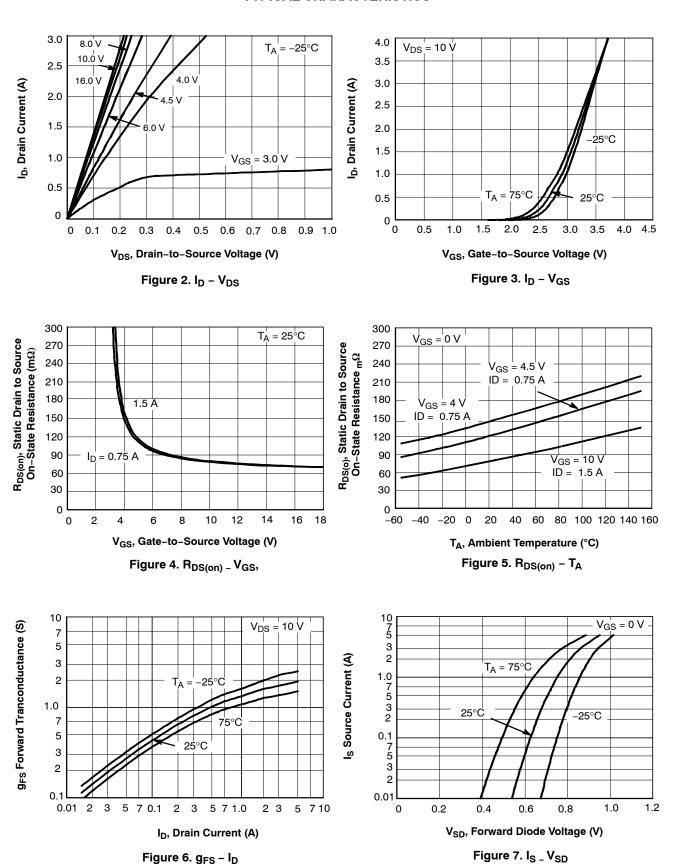


Figure 1. Switching Time Test Circuit

#### **TYPICAL CHARACTERISTICS**



# TYPICAL CHARACTERISTICS (continued)

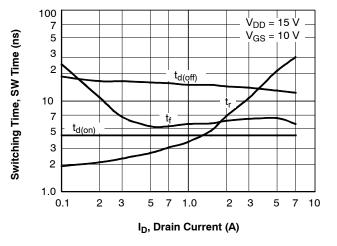


Figure 8. Time (SW) - I<sub>D</sub>

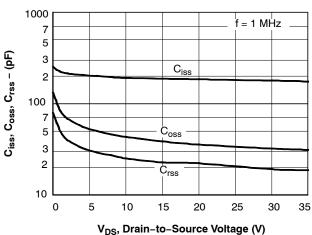


Figure 9.  $V_{DS}$  –  $C_{iss}$ ,  $C_{oss}$ ,  $C_{rss}$ 

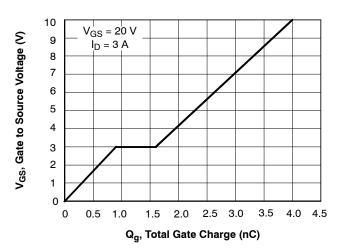
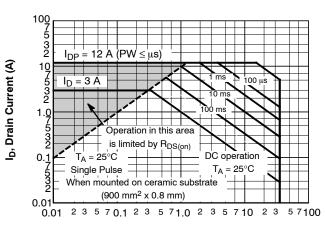


Figure 10. V<sub>GS</sub> - Q<sub>g</sub>



V<sub>DS</sub>, Drain to Source Voltage (V)

Figure 11. S O A

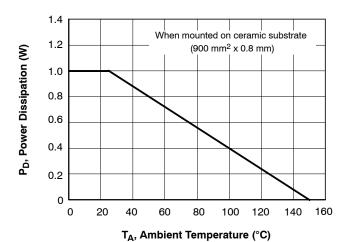


Figure 12. P<sub>D</sub> - T<sub>A</sub>

# TYPICAL CHARACTERISTICS (continued)

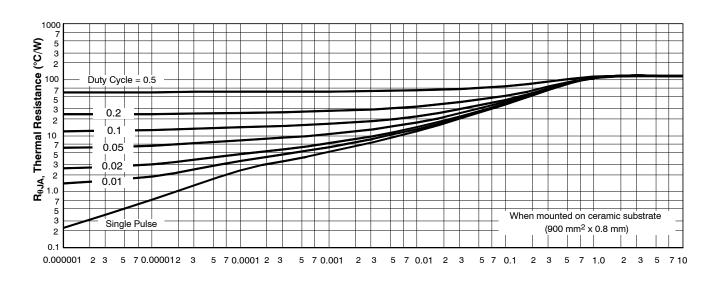


Figure 13.  $R_{\theta JA}$  – Pulse Time

Pt Pulse Time (s)

#### **DEVICE ORDERING INFORMATION**

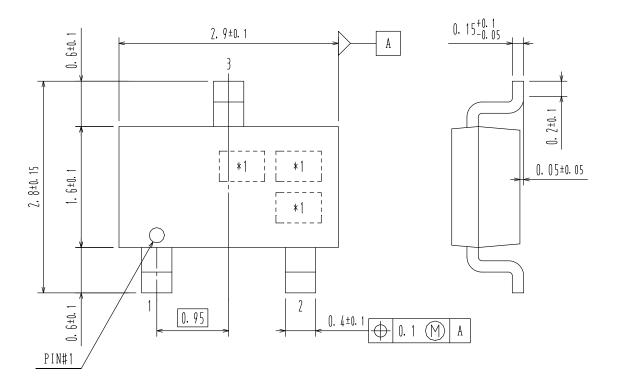
Device	Marking	Package	Shipping <sup>†</sup>
CPH3455-TL-H	LM	CPH3 SC-59, SOT-23, TO-236 (Pb-Free / Halogen Free)	3000 / Tape & Reel

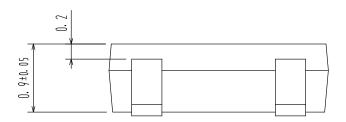
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <a href="https://example.com/BRD8011/D">BRD8011/D</a>.

<sup>\*</sup>Note on usage : Since the CPH3455 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

CPH3 CASE 318BA ISSUE O

**DATE 30 NOV 2011** 





DOCUMENT NUMBER:	98AON65437E	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	СРНЗ		PAGE 1 OF 1

ON Semiconductor and III are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales